

General Description

The AO6407 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

Features

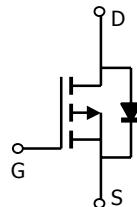
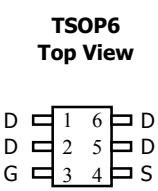
V_{DS} (V) = -20V

I_D = -5 A

$R_{DS(ON)} < 45m\Omega$ ($V_{GS} = -4.5V$)

$R_{DS(ON)} < 60m\Omega$ ($V_{GS} = -2.5V$)

$R_{DS(ON)} < 85m\Omega$ ($V_{GS} = -1.8V$)



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current ^A	I_D	-5.5	A
$T_A=70^\circ C$		-4.5	
Pulsed Drain Current ^B	I_{DM}	-30	
Power Dissipation ^A	P_D	2	W
$T_A=70^\circ C$		1.44	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	47.5	62.5	°C/W
Steady-State		74	110	°C/W
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	37	50	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-20			V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}, V_{GS}=0\text{V}$	$T_J=55^\circ\text{C}$	-1	-5	μA	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 8\text{V}$			± 100	nA	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.3	-0.55	-1	V	
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$	-25			A	
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5\text{V}, I_D=-5\text{A}$		34	45	$\text{m}\Omega$	
		$T_J=125^\circ\text{C}$	48	60			
				60			
V_{SD}	Diode Forward Voltage	$V_{DS}=-2.5\text{V}, I_D=-4\text{A}$		46	60	$\text{m}\Omega$	
		$V_{GS}=-1.8\text{V}, I_D=-2\text{A}$		61	85	$\text{m}\Omega$	
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-5\text{A}$	7	14		S	
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.78	-1	V	
I_s	Maximum Body-Diode Continuous Current				-2.2	A	
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$		1180		pF	
C_{oss}	Output Capacitance			176		pF	
C_{rss}	Reverse Transfer Capacitance			142		pF	
R_g	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		15		Ω	
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, I_D=-5\text{A}$		13		nC	
Q_{gs}	Gate Source Charge			1.2		nC	
Q_{gd}	Gate Drain Charge			3.6		nC	
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=-4.5\text{V}, V_{DS}=-10\text{V}, R_L=2.0\Omega, R_{\text{GEN}}=3\Omega$		13.2		ns	
t_r	Turn-On Rise Time			21		ns	
$t_{\text{D(off)}}$	Turn-Off Delay Time			93		ns	
t_f	Turn-Off Fall Time			46		ns	
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		43		ns	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		21		nC	

A: The value of R_{0JA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{0JA} is the sum of the thermal impedance from junction to lead R_{0JL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

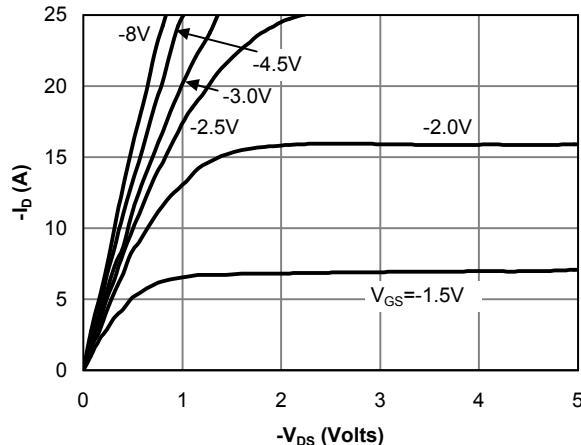


Fig 1: On-Region Characteristics

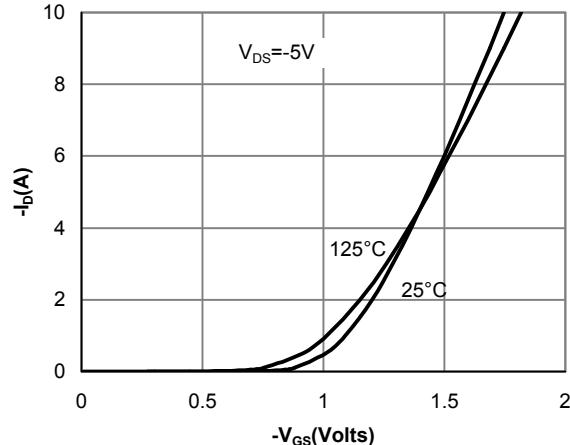


Figure 2: Transfer Characteristics

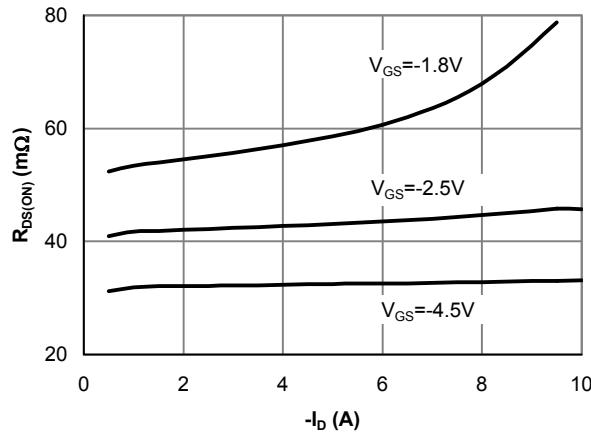


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

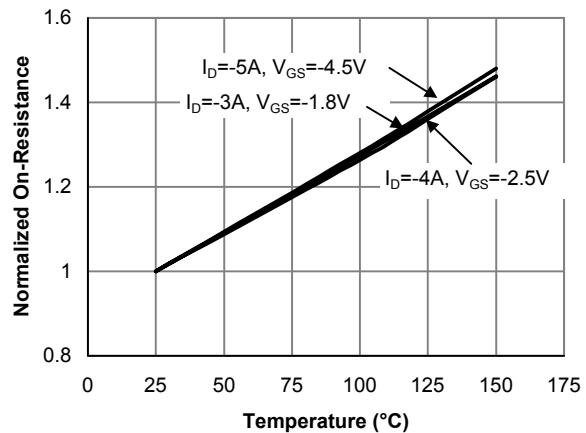


Figure 4: On-Resistance vs. Junction Temperature

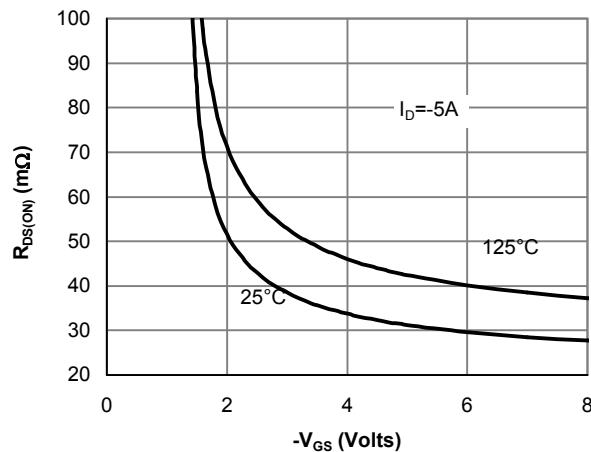


Figure 5: On-Resistance vs. Gate-Source Voltage

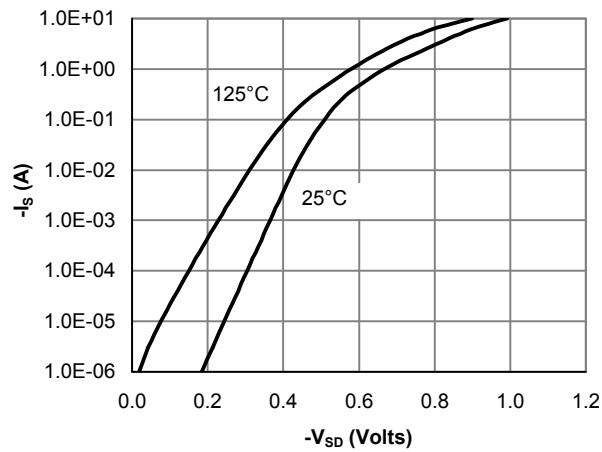


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

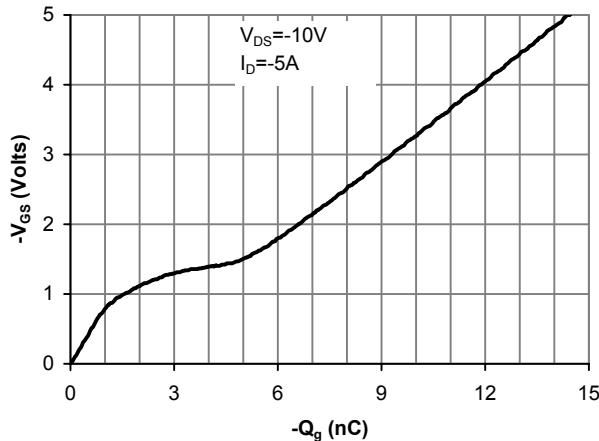


Figure 7: Gate-Charge Characteristics

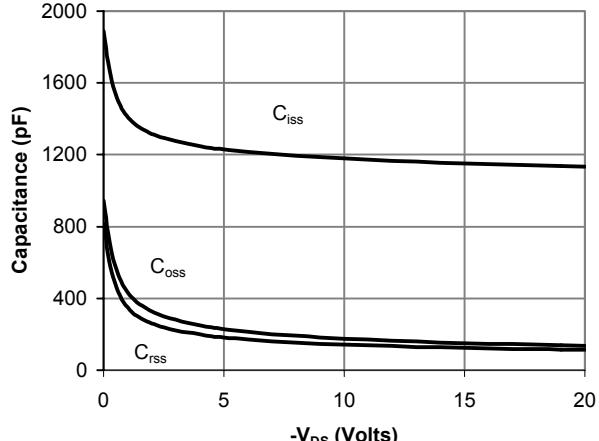


Figure 8: Capacitance Characteristics

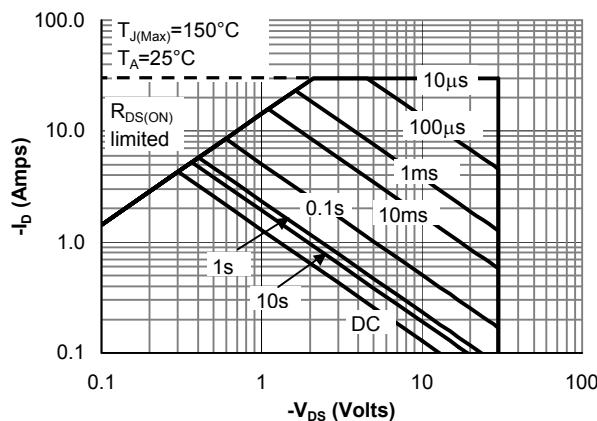


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

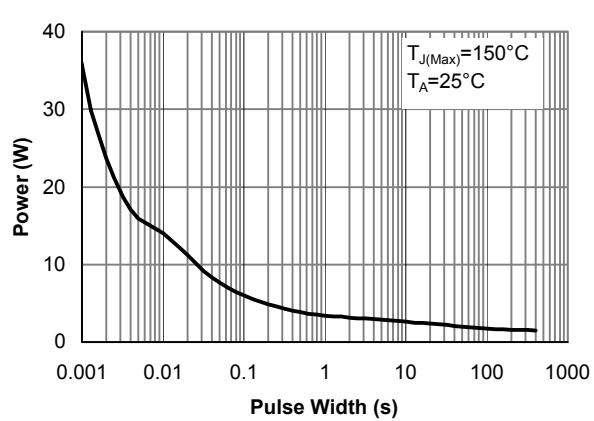


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

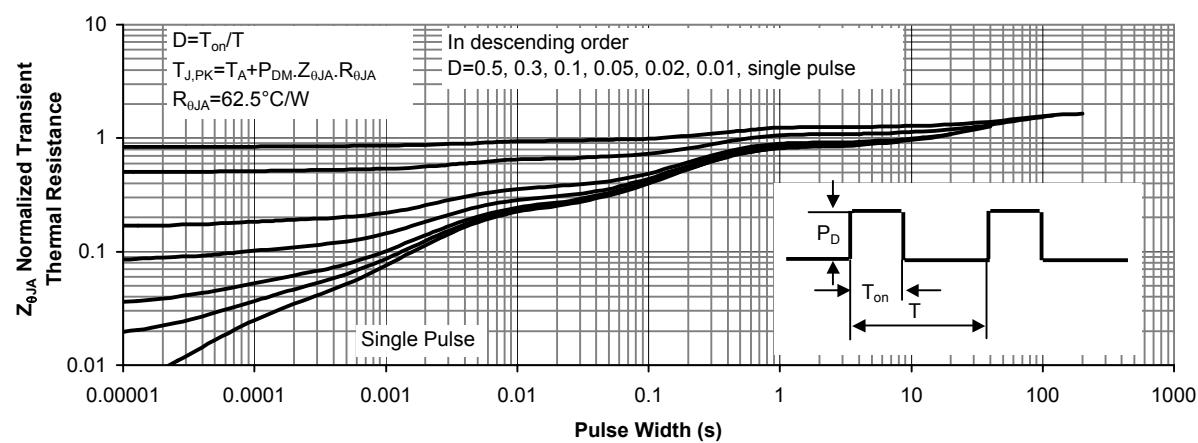
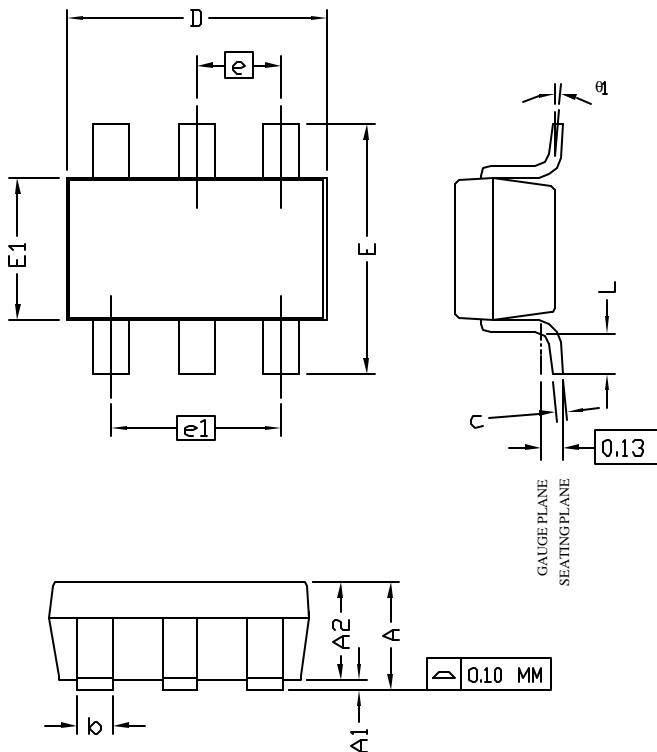


Figure 11: Normalized Maximum Transient Thermal Impedance



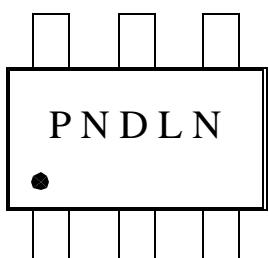
TSOP-6 Package Data



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
A	1.00	—	1.25
A1	0.00	—	0.10
A2	1.00	1.10	1.15
b	0.35	0.40	0.50
c	0.10	0.13	0.20
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.60	1.80	2.00
e	0.95 BSC		
e1	1.90 BSC		
L	0.37	—	—
θ_1	1°	5°	8°

NOTE:
1. LEAD FINISH: 150 MICROINCHES (3.8 μ m) MIN.
THICKNESS OF Tin/Lead (SOLDER) PLATED ON LEAD
2. TOLERANCE ± 0.100 mm (4 mil) UNLESS OTHERWISE
SPECIFIED
3. COPLANARITY : 0.100 mm
4. DIMENSION L IS MEASURED IN GAGE PLANE

PACKAGE MARKING DESCRIPTION

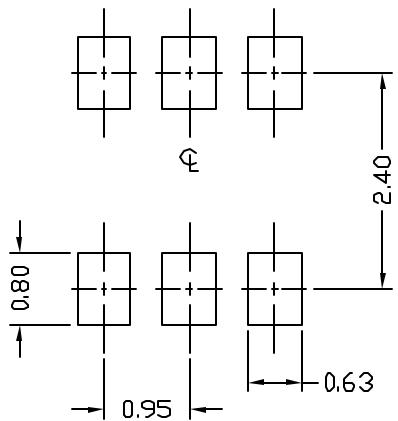


TSOP-6 PART NO. CODE

PART NO.	CODE
AO6407	D7

NOTE:
P N - PART NUMBER CODE.
D - YEAR AND WEEK CODE.
L N - ASSEMBLY LOT CODE, FAB AND
ASSEMBLY LOCATION CODE.

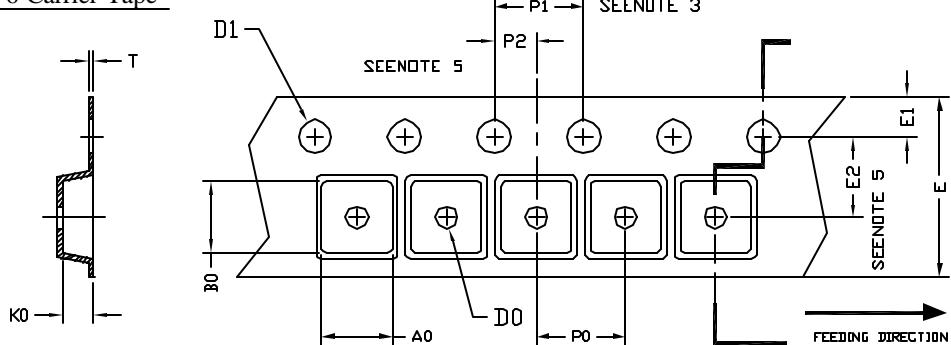
RECOMMENDED LAND PATTERN





TSOP-6 Tape and Reel Data

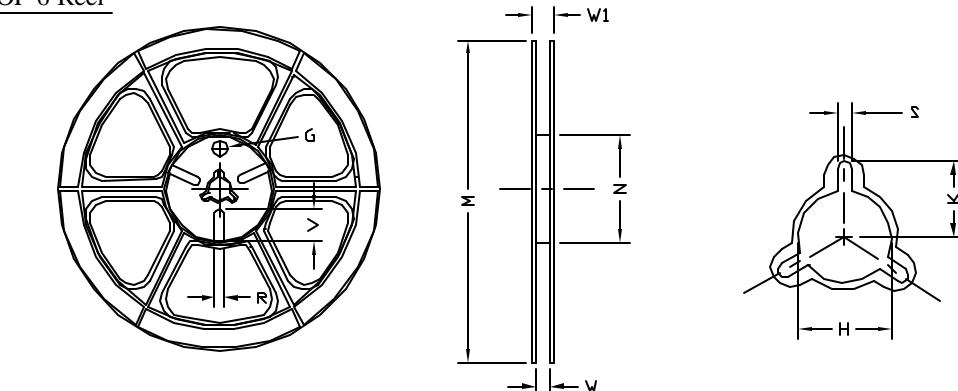
TSOP-6 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23 (B mm)	3.15 ±0.10	3.27 ±0.10	1.34 ±0.10	1.10 ±0.01	1.50 +0.10	8.00 ±0.20	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.10	0.25 ±0.05

TSOP-6 Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8 mm	Ø180	Ø180.00 ±0.50	Ø60.50	9.00 ±0.30	11.40 ±1.00	Ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	Ø9.00	5.00	18.00

TSOP-6 Tape

Leader / Trailer
& Orientation

